

# THE MULTIPLE IMMUNOLOCALIZATION METHOD USING AU MARKERS FOR LOW VOLTAGE STEM

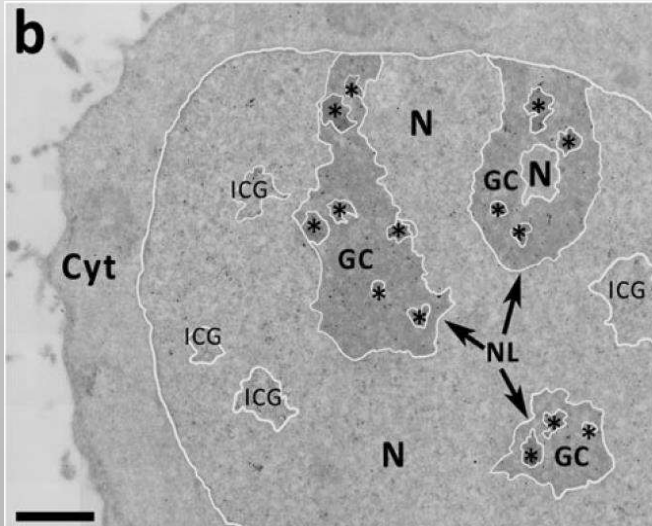
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Faculty of Science, Charles University, Prague  
Czech Republic  
Frantisek.Kitzberger@paru.cas



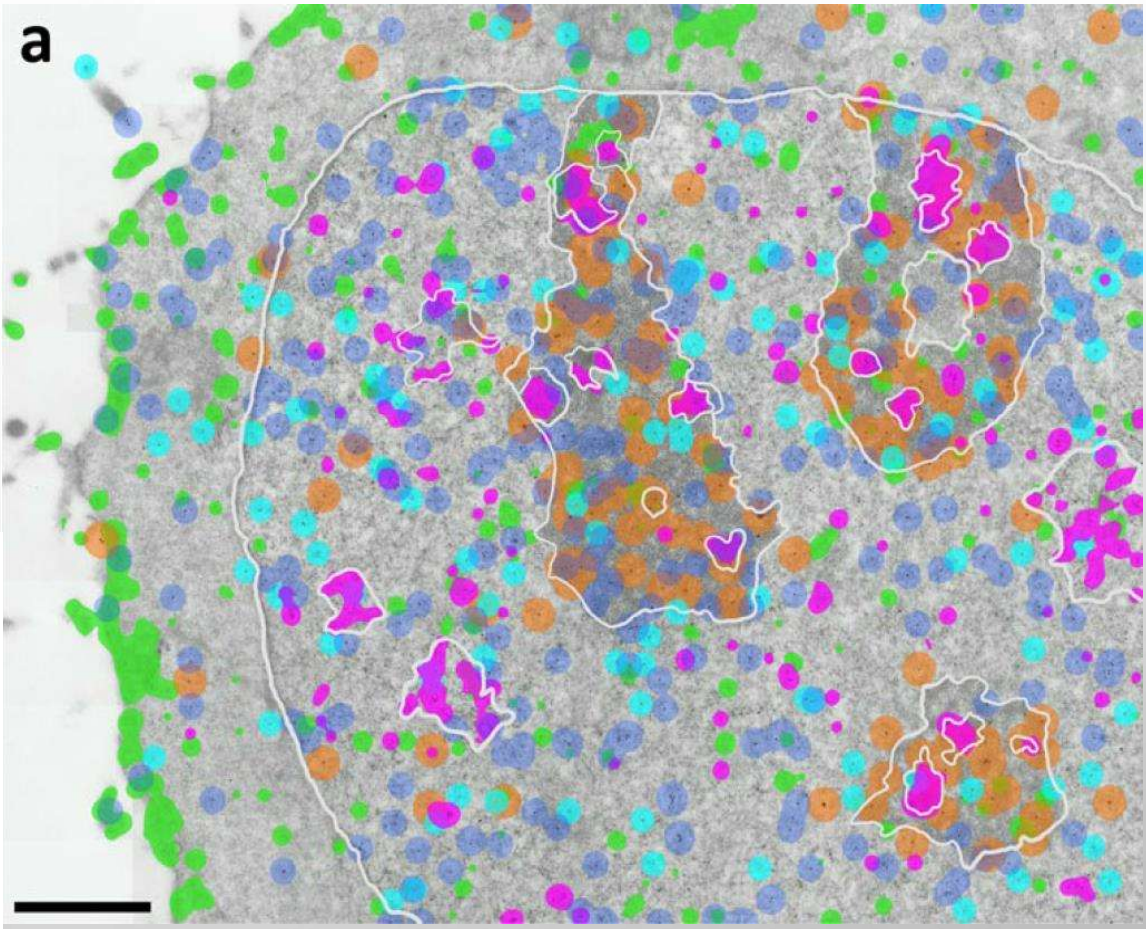
# MULTIPLE IMMUNOLOCALISATION

- MORE ANTIGENS CAN BE DETECTED SIMULTANEOUSLY BY USING DIFFERING IMMUNOMARKERS - EG. DIFFERENT DIAMETERS (5 AND 15 NM)
- LIMITATION: NUMBER OF SUITABLE MARKERS.
- IN TEM AU NANOPARTICLES WITH DIFFERENT SHAPES



**c**

Sm	■	PdC
PIP2	■	AuNR
B23	●	AgAu
SMC2	●	Au12
actin	●	Au6

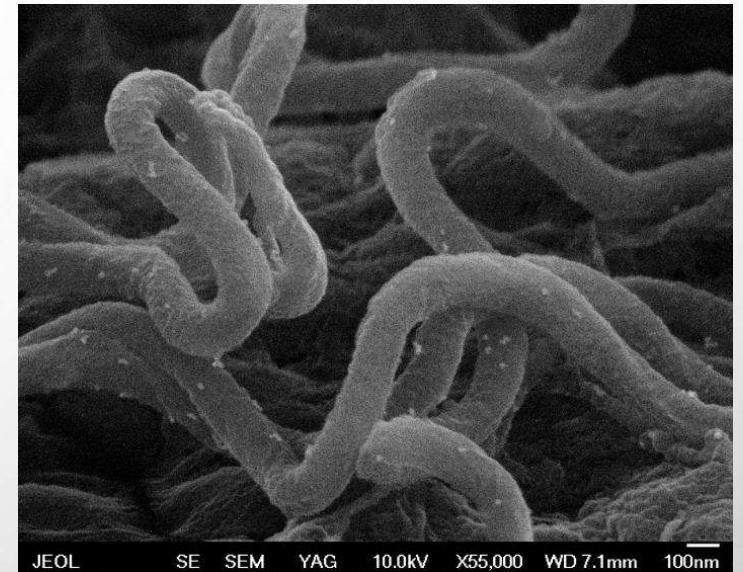


(Philimonenko VV et al. 2014, Histochem Cell Biol. 141(3):241)

# MULTIPLE IMMUNOLOCALISATION IN HRSEM

BSE IMAGING FOR THE DETECTION OF IMMUNOLABELING RESULTS:

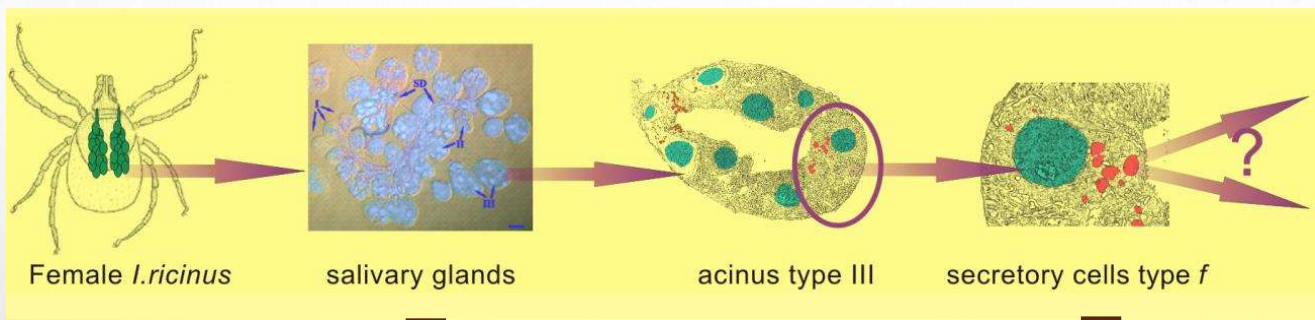
- POSSIBILITY TO WORK WITH LOW VOLTAGES (0,5-5 KV)
- SUFFICIENT RESOLUTION POWER TO DETECT 5 NM METAL NPs
- INTENSITY OF THE BSE SIGNAL DEPENDS ON THE ATOMIC NUMBER Z OF THE NP
- BETTER TOPOGRAPHIC CONTRAST
- LESS SENSITIVE TO THE CONTAMINATION
- LESS SENSITIVE TO THE CHARGING EFFECT



*Salivary glands of ticks infected with Borrelia*

# MULTIPLE IMMUNOLABELING IN HRSEM

- USING NPs OF VARIOUS METALS CONJUGATED WITH SECONDARY ANTIBODIES AS MARKERS



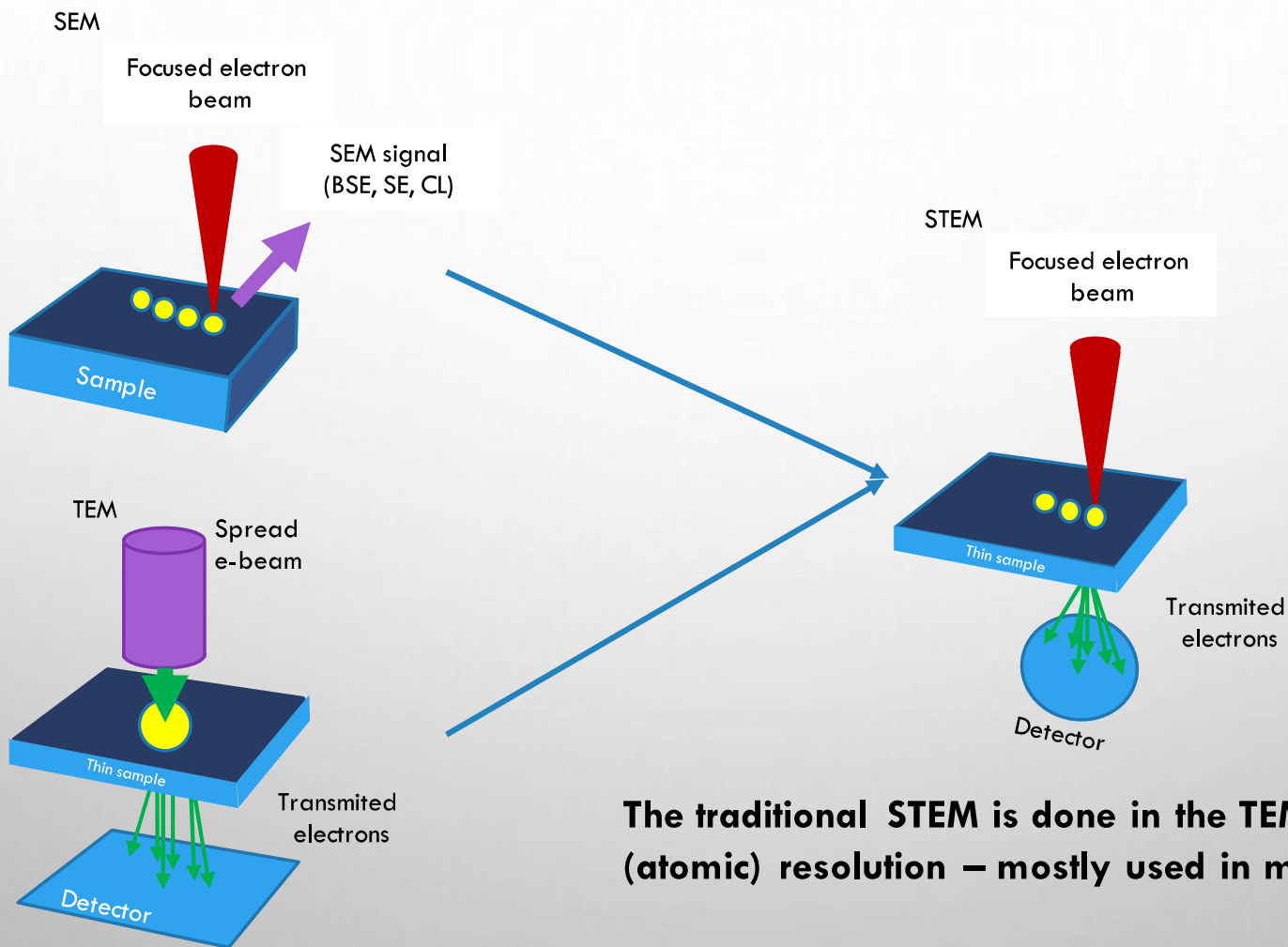
Mannose (cytoplasm)

Sm protein (nucleus)

**Specimen preparation:**  
Chemical fixation (4% FA and 0,5% GA)  
Dehydration (ethanol, PLT)  
Embedding (Lowicryl K4M, UV polymerized, -35°C)

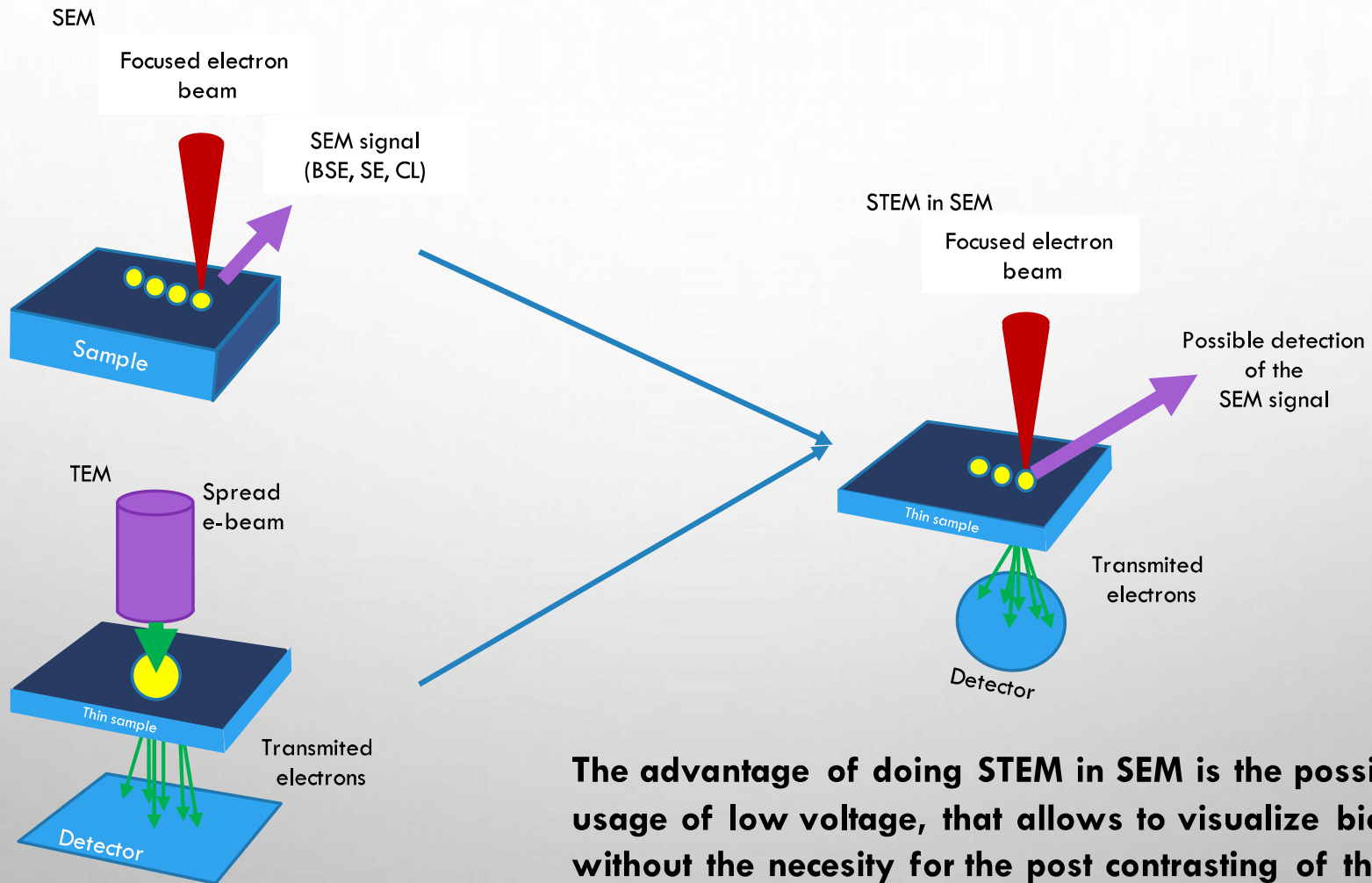
Immunolabelling:  
**Primary antibodies**  
Biotinylated ConA  
Human anti Sm  
**Secondary antibodies**  
Streptavidin Pd conjugate (9 nm)  
Anti-human IgG gold (10 nm)

# WHAT IS STEM?



**The traditional STEM is done in the TEM and has the best possible (atomic) resolution – mostly used in material sciences**

# WHAT IS STEM?



**The advantage of doing STEM in SEM is the possibility of usage of low voltage, that allows to visualize biological specimens without the necessity for the post contrasting of the sections**

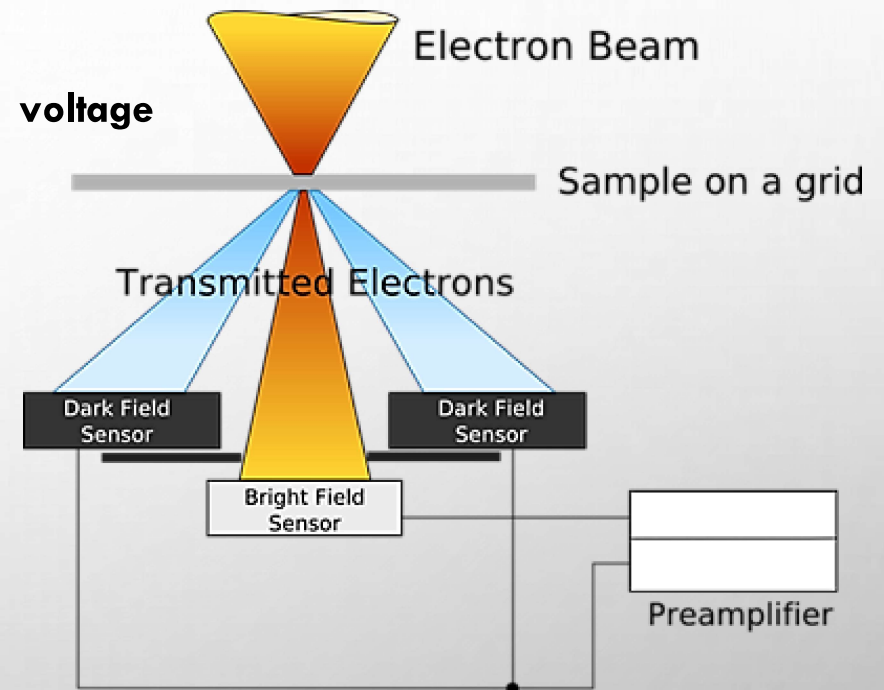
# MULTIPLE IMMUNOLABELING IN LOW-VOLTAGE STEM

## STEM in SEM allows:

- Using low accelerating voltages ranging between 1-30 kV
- Visualization of non-contrasted ultrathin sections
- Detecting simultaneously BSE and transmitted electrons
- Choose the depth of signal origin by selection of accelerating voltage

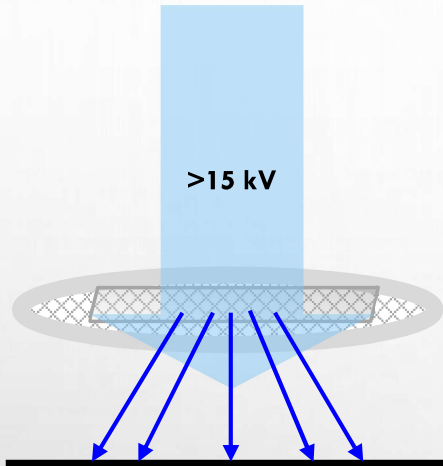
- LABELING ON BOTH SIDES OF THE ULTRATHIN SECTION BY ANTIBODIES CONJUGATED WITH AU-NPS OF DIFFERENT DIAMETERS IN TEM (Pasolli et al, 1994) – USEFUL IF WE HAVE PRIMARY ANTIBODIES OF THE SAME ANIMAL

- DETECTION AND DIFFERENTIATION OF AU-NPs ON BOTH SIDES OF THE SECTION BY LOW-VOLTAGE STEM AND BSE IMAGING IN SEM USING TWO ACCELERATING VOLTAGES (Nebesářová et al, 2016)

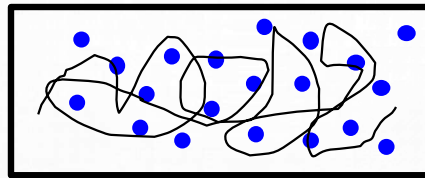


# Ideal workflow...

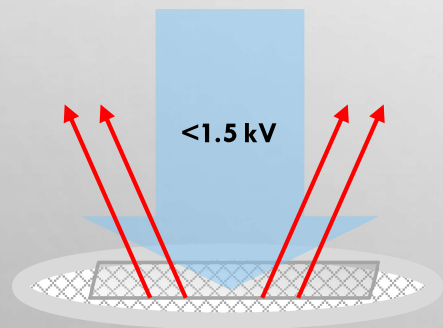
STEM signal



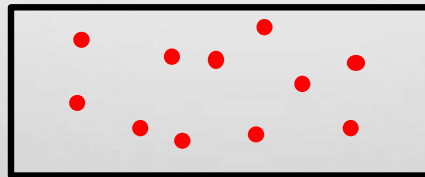
Electrons accelerated by higher accelerating voltage can penetrate section  
- We can see all markers and ultrastructure



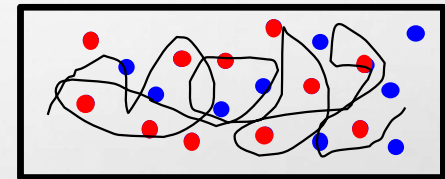
BSE signal



Electrons accelerated by lower voltage do not penetrate the section – we can see only the BSE signal from surface



After subtracting the BSE detected markers from the STEM detected ones, we know which markers are on the bottom of the section

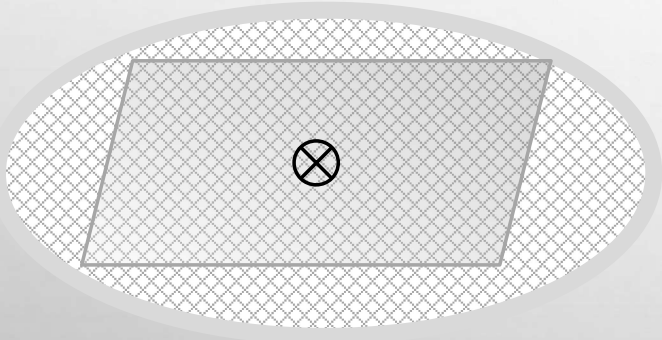




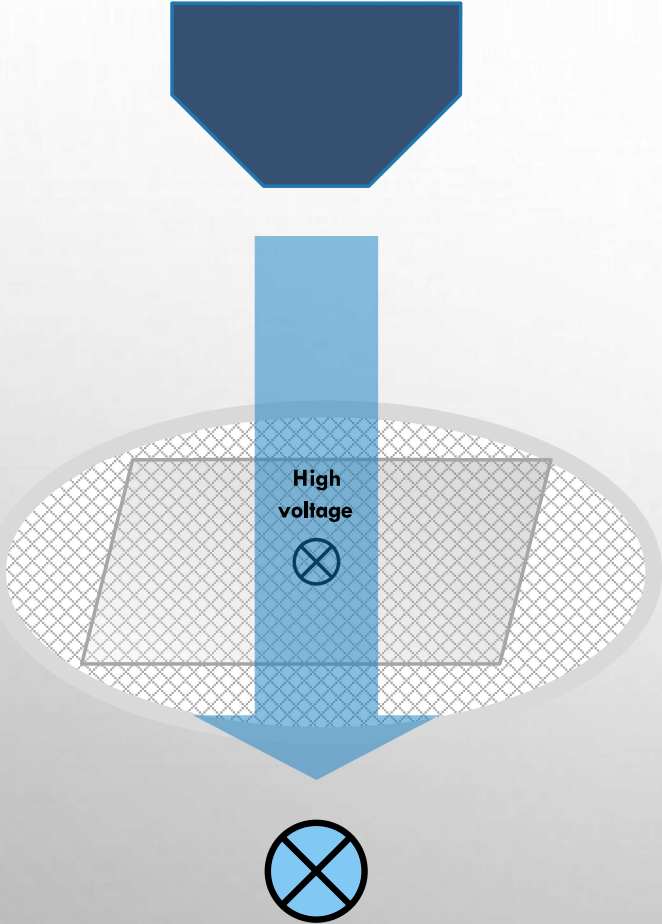
# Real workflow – step by step



1) Find the object of interest

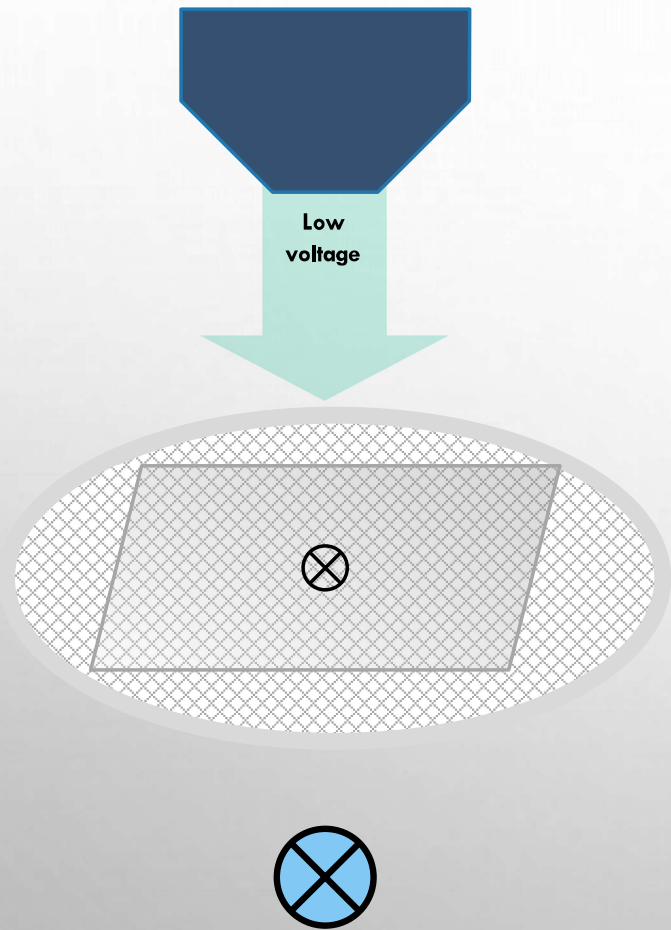


# Real workflow – step by step



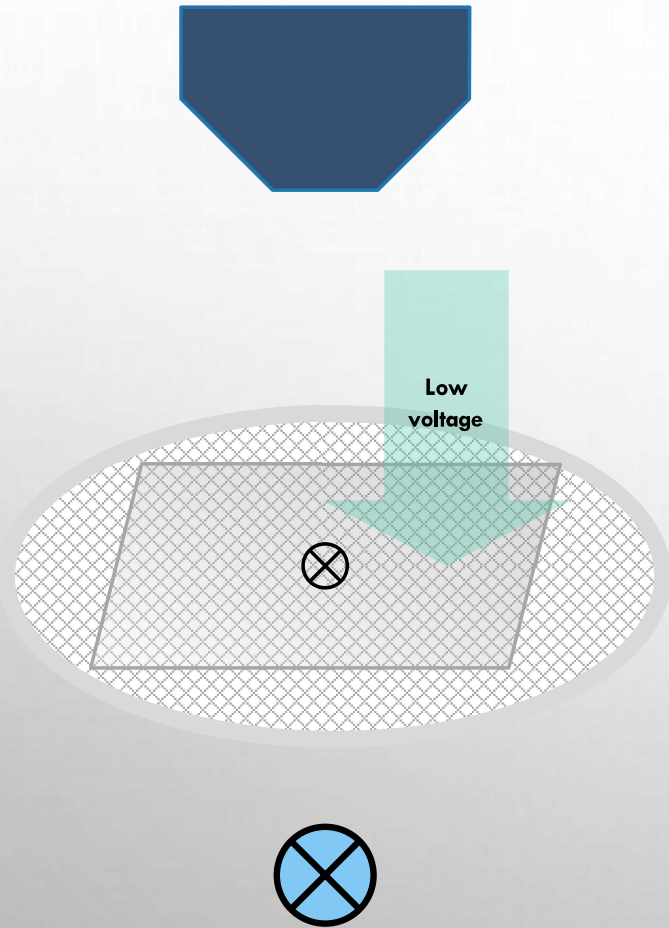
- 1) Find the object of interest
- 2) Look at it under high accelerating voltage ( $>15\text{kV}$ ) – on STEM  
- you will see everything

## Real workflow – step by step



- 1) Find the object of interest
- 2) Look at it under high accelerating voltage ( $>15\text{kV}$ ) – on STEM  
- you will see everything
- 3) Switch to low accelerating voltage ( $<2\text{kV}$ )

## Real workflow – step by step



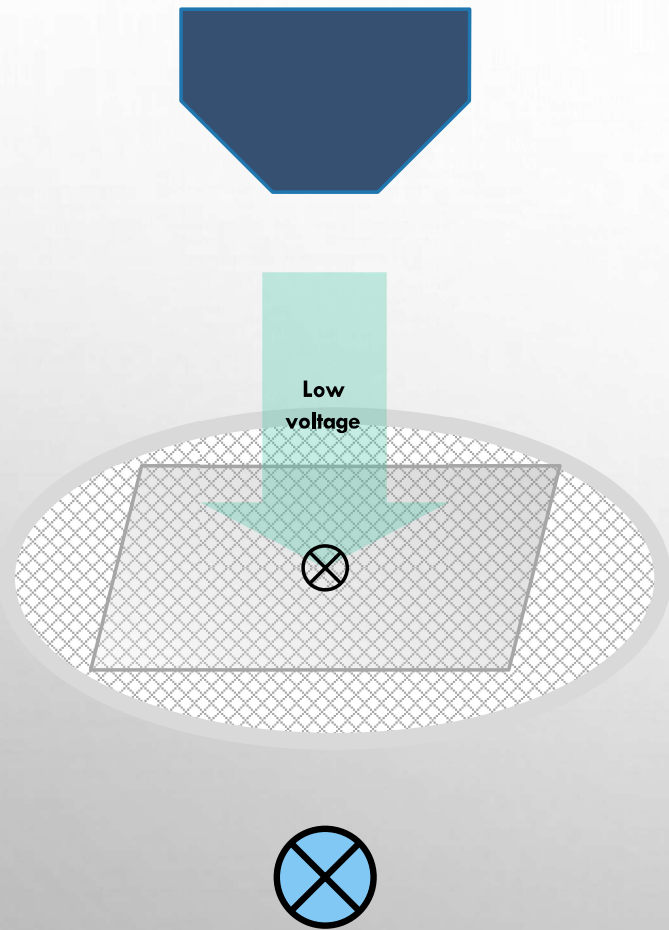
**1) Find the object of interest**

**2) Look at it under high accelerating voltage ( $>100kV$ ) -- as SEM  
- you will see everything**

**3) Switch to low accelerating voltage ( $<20kV$ )**

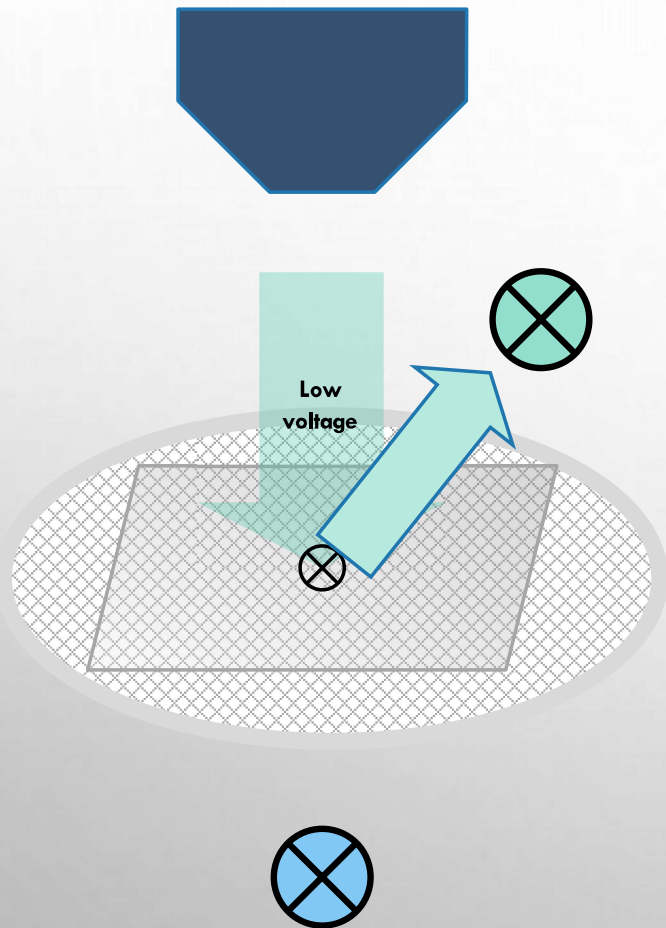
**4) Find out that your beam shifted to different position and defocused**

## Real workflow – step by step



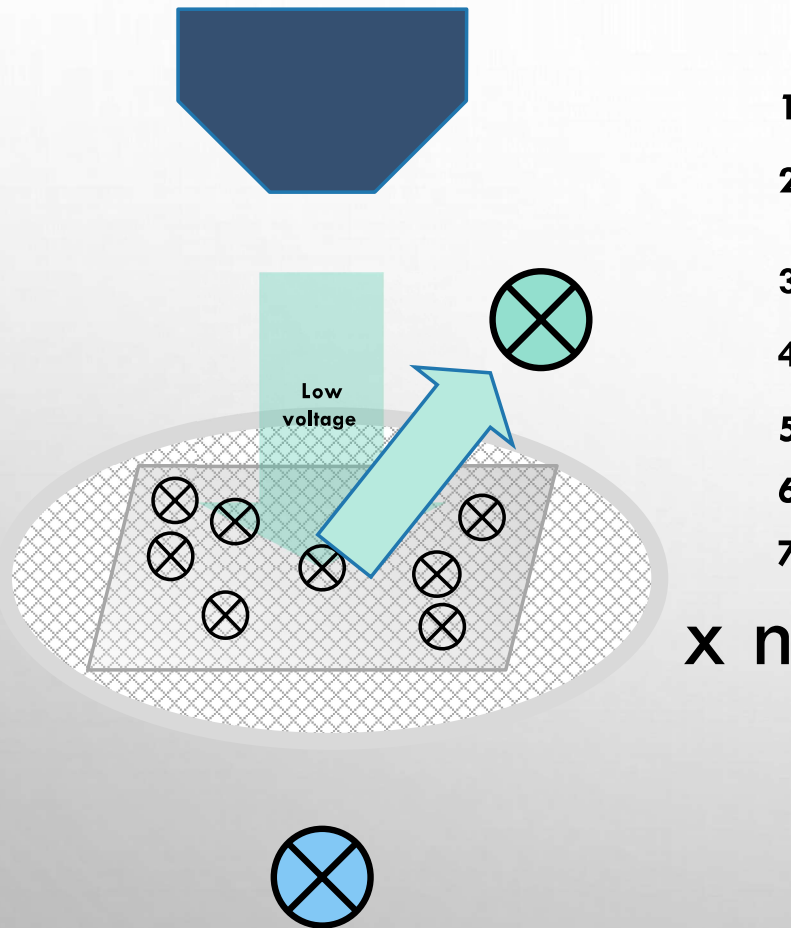
- 1) Find the object of interest
- 2) Look at it under high accelerating voltage ( $>15\text{kV}$ ) – on STEM  
- you will see everything
- 3) Switch to low accelerating voltage ( $<2\text{kV}$ )
- 4) Find out that your beam shifted to different position and defocused
- 5) Refocus the beam and shift it back to the original position

## Real workflow – step by step



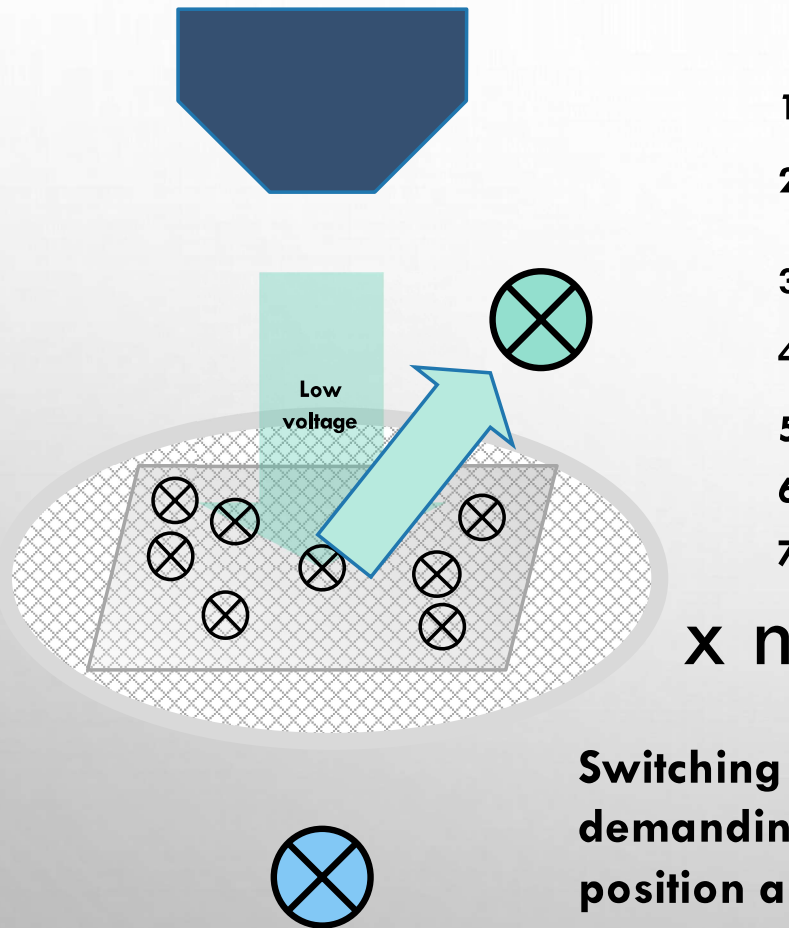
- 1) Find the object of interest
- 2) Look at it under high accelerating voltage ( $>15\text{kV}$ ) – on STEM  
- you will see everything
- 3) Switch to low accelerating voltage ( $<2\text{kV}$ )
- 4) Find out that your beam shifted to different position and defocused
- 5) Refocus the beam and shift it back to the original position
- 6) Look at the object of interest on the BSE – see surface

## Real workflow – step by step



- 1) Find the object of interest
- 2) Look at it under high accelerating voltage ( $>15\text{kV}$ ) – on STEM  
- you will see everything
- 3) Switch to low accelerating voltage ( $<2\text{kV}$ )
- 4) Find out that your beam shifted to different position and defocused
- 5) Refocus the beam and shift it back to the original position
- 6) Look at the object of interest on the BSE – see surface
- 7) Repeat steps 1-6 for each object of interest on each sample you have

## Real workflow – step by step



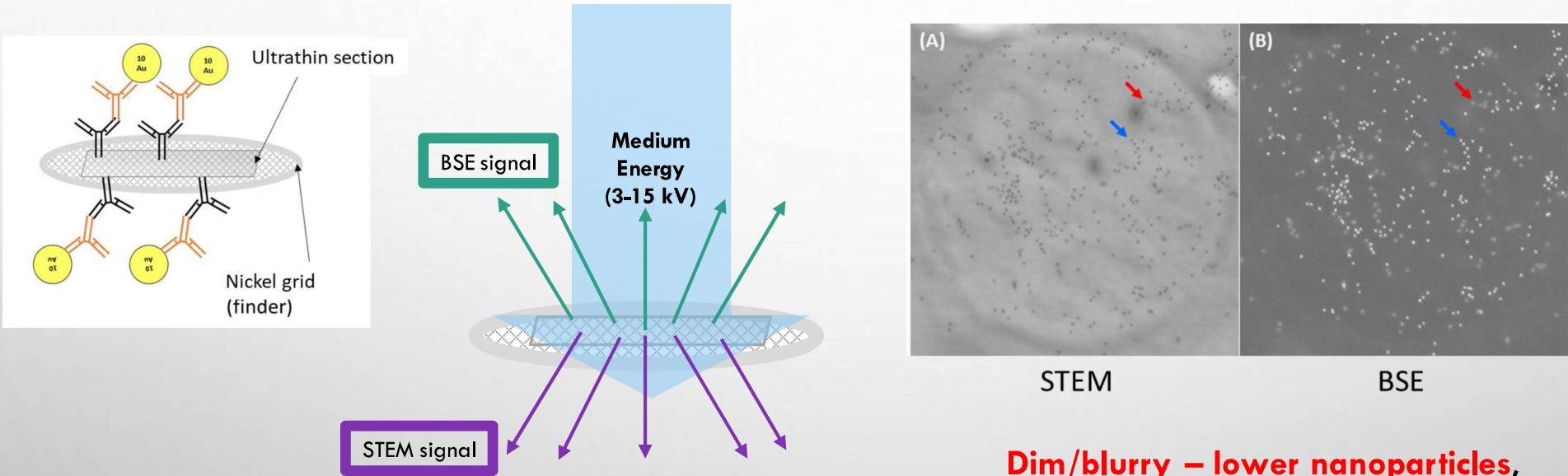
- 1) Find the object of interest
- 2) Look at it under high accelerating voltage ( $>15\text{kV}$ ) – on STEM  
- you will see everything
- 3) Switch to low accelerating voltage ( $<2\text{kV}$ )
- 4) Find out that your beam shifted to different position and defocused
- 5) Refocus the beam and shift it back to the original position
- 6) Look at the object of interest on the BSE – see surface
- 7) Repeat steps 1-6 for each object of interest on each sample you have

Switching between 2 accelerating voltages is laborious and time demanding due to the constant shifting of the beam to correct position and the necessity of refocusing. This also may lead to higher radiation damage and formation of contaminations



# MULTIPLE IMMUNOLABELING IN LOW-VOLTAGE STEM

WORKFLOW OF THE METHOD USING ONLY ONE ACCELERATING VOLTAGE



**Dim/blurry – lower nanoparticles,**  
**Bright/sharp – upper nanoparticles**

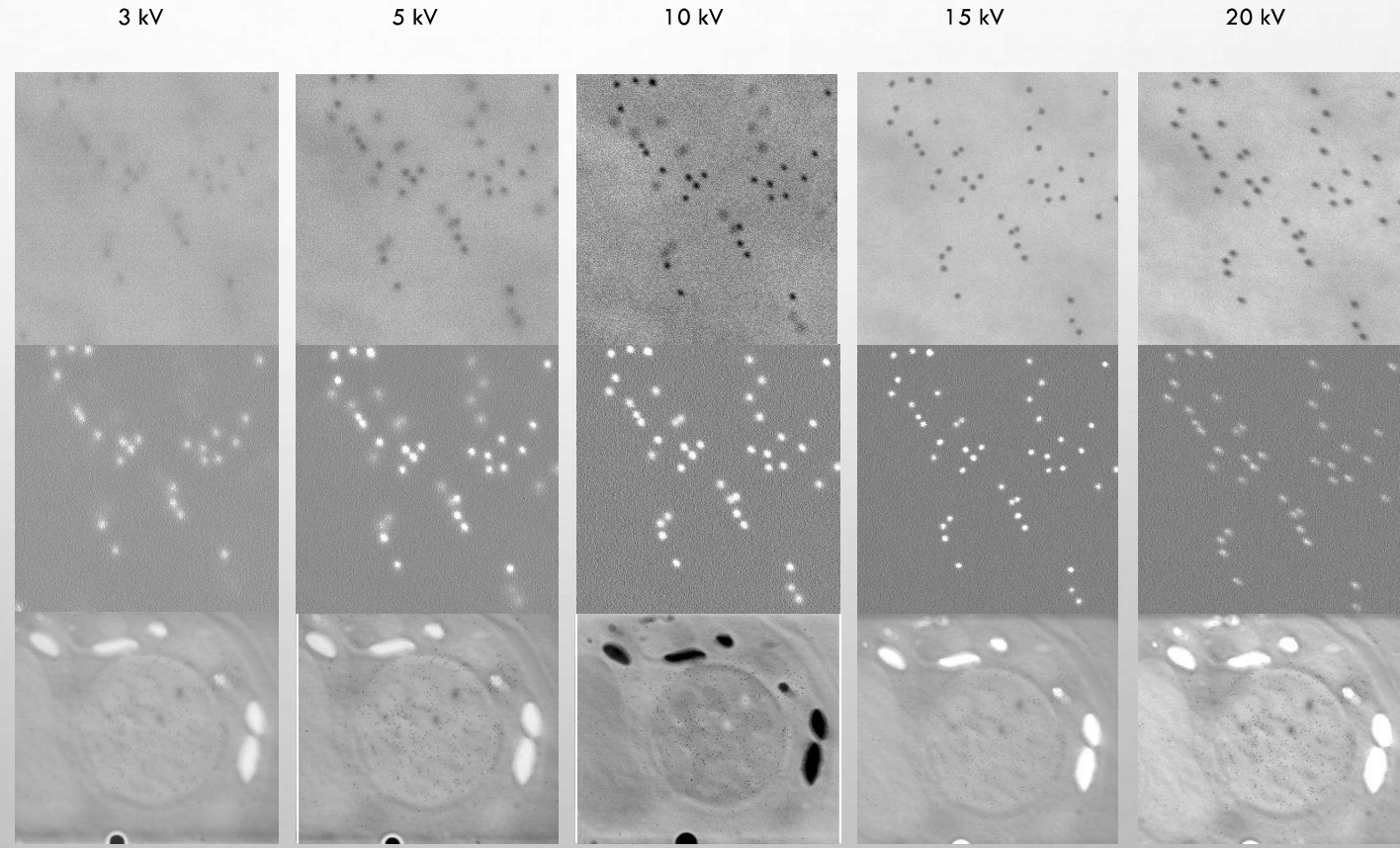
Gold nanoparticles (10 nm) on the nucleus of *C. Velia*, (non-specific reaction) 5kV, 15.68 $\mu$ s, 37 000x, 100 nm section

F. Kitzberger et al, 2023, in press

# MULTIPLE IMMUNOLABELING IN LOW-VOLTAGE STEM

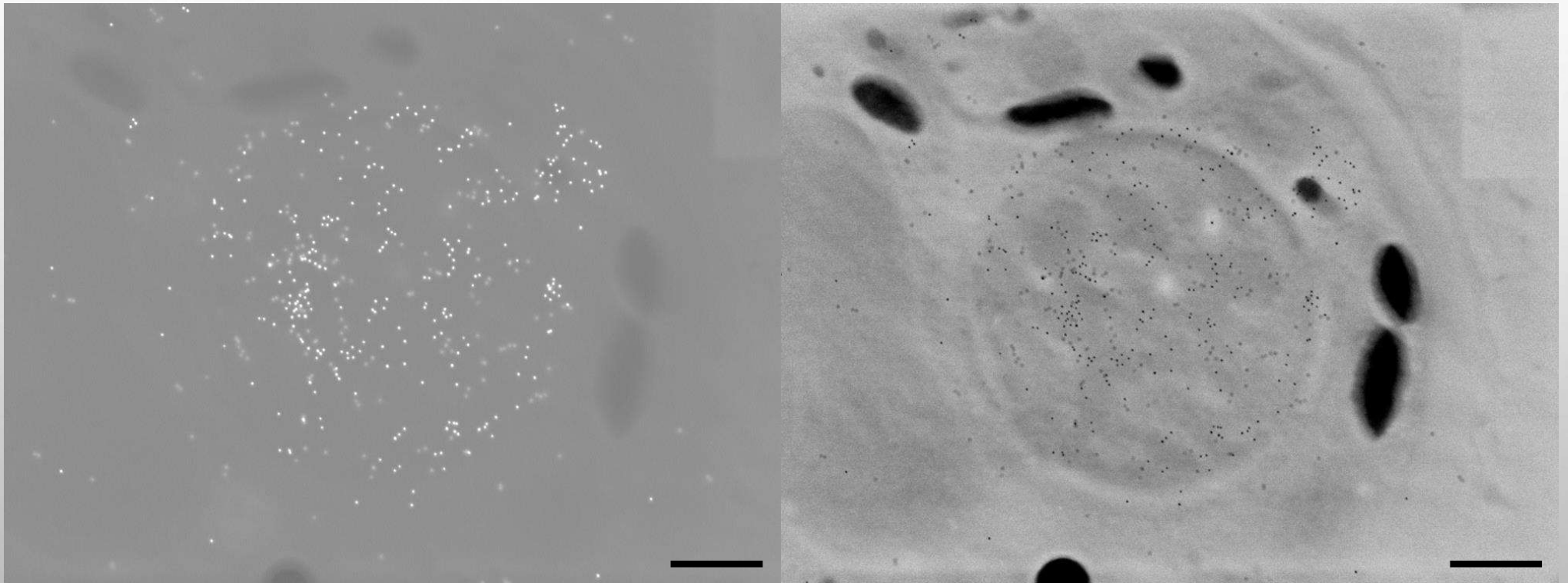
Propper setting of acquisition parameters (accelerating voltage, acquisition time, magnification) allows us to get all necessary information (ultrastructure, differentiate top and bottom NP) from one run – no need to switch the accelerating voltage → no need to refocus and shift the beam back to the proper position – faster and more gentle.

**Comparison of different accelerating voltages for simultaneous imaging of the top and bottom nanoparticles on a 100 nm section**



# MULTIPLE IMMUNOLABELING IN LOW-VOLTAGE STEM

THE OPTIMAL ACCELERATING VOLTAGE FOR 100 NM SECTION LAYS BETWEEN 5 AND 10 KV



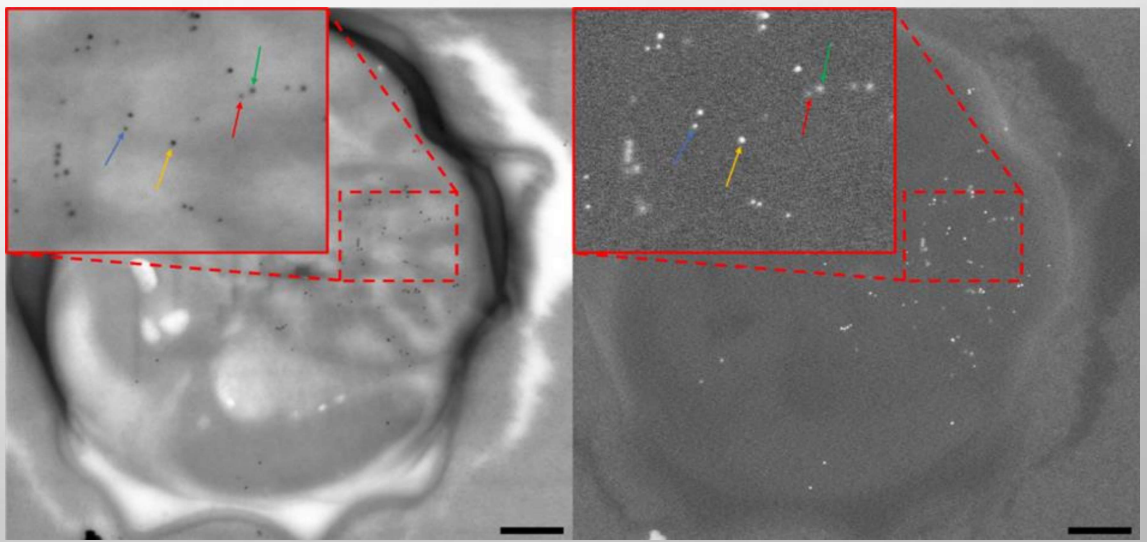
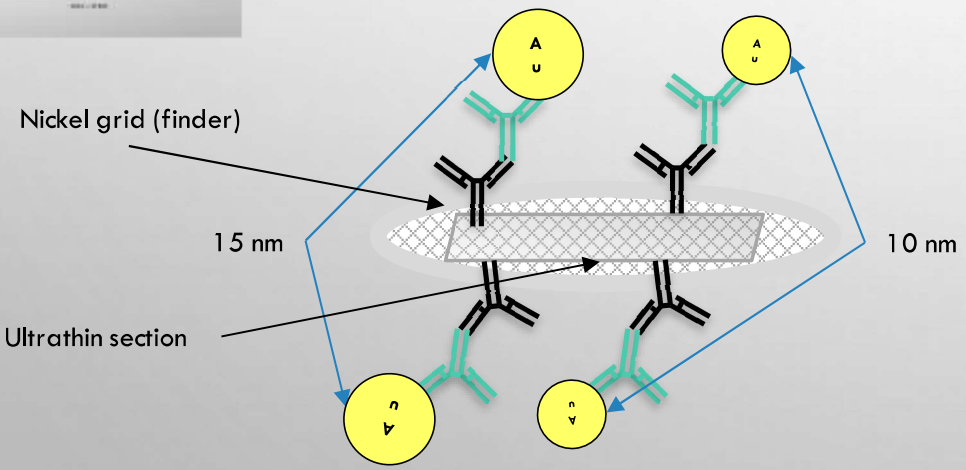
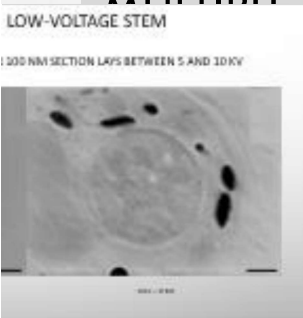
5kV – BSE

10kV – STEM

# MULTIPLE IMMUNOLABELING IN LOW-VOLTAGE STEM

SIMULTANEOUS DETECTION OF TWO Au MARKERS ON BOTH SIDES OF THE SECTION  
 =  
 MULTIPLE IMMUNOLOCALISATION OF FOUR REGIONS OF INTEREST

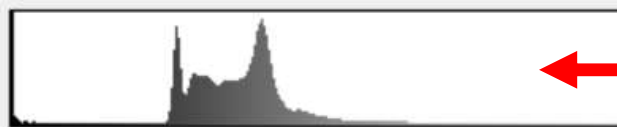
15 nm top	Big	Bright	Sharp
10 nm top	Small	Bright	Sharp
15 nm bottom	Big	Dim	Blurry
10 nm bottom	Small	Dim	Blurry



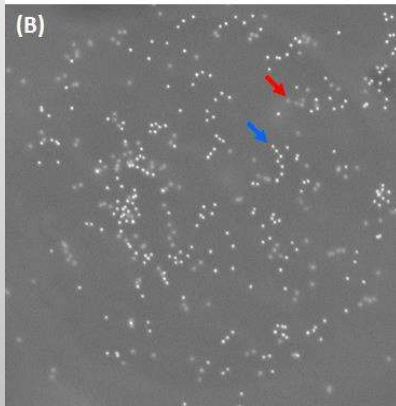
# MULTIPLE IMMUNOLABELING IN LOW-VOLTAGE STEM

THE ENHANCEMENT OF THE VISUAL DIFFERENCE BETWEEN BOTTOM AND TOP Au NPs  
WITH THE HELP OF IMAGE PROCESSING

BSE image → Import to ImageJ/FIJI → Adjust the B/W threshold → Adjust the B/W threshold → Upper NPs will transform to donut shape



B/W threshold histogram

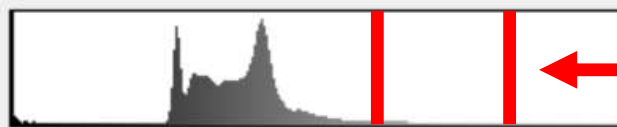


Gold nanoparticles (10 nm) on the nucleus of *C. Velia*, (non-specific reaction) 5kV, 15.68 $\mu$ s, 37 000x, 100 nm section

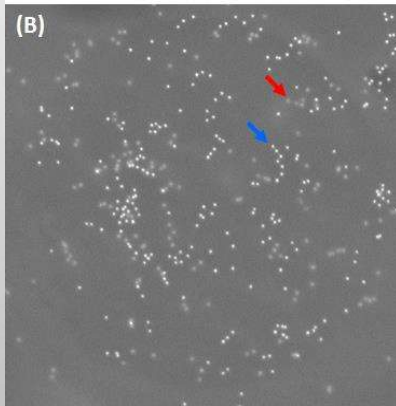
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BSE image → Import to ImageJ/FIJI → Adjust the B/W threshold → Adjust the B/W threshold → Upper NPs will transform to donut shape



adjust the minima and maxima of the B/W threshold

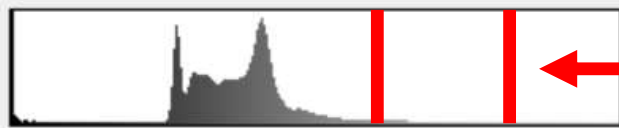


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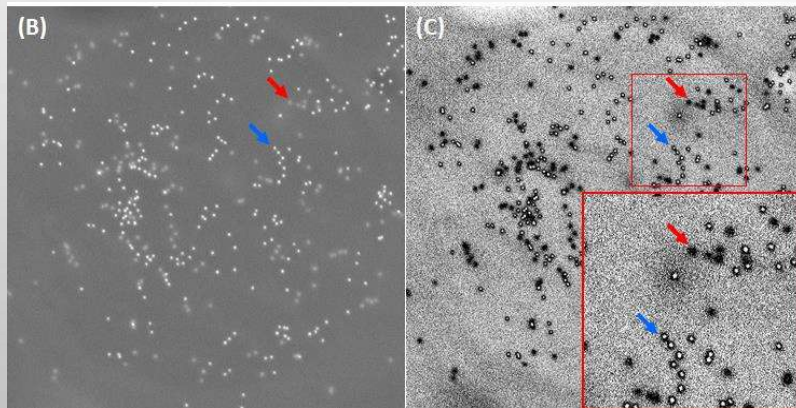
# MULTIPLE IMMUNOLABELING IN LOW-VOLTAGE STEM

THE ENHANCEMENT OF THE VISUAL DIFFERENCE BETWEEN BOTTOM AND TOP Au NPs  
WITH THE HELP OF IMAGE PROCESSING

BSE image → Import to ImageJ/FIJI → Adjust the B/W threshold → Upper NPs will transform to donut shape Adjust



adjust the minima and maxima of the B/W threshold

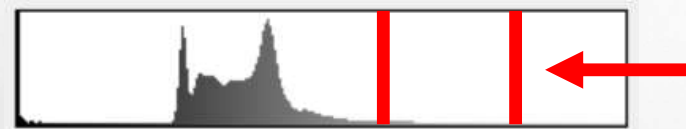


Gold nanoparticles (10 nm) on the nucleus of *C. Velia*, (non-specific reaction) 5kV, 15.68 $\mu$ s, 37 000x, 100 nm section

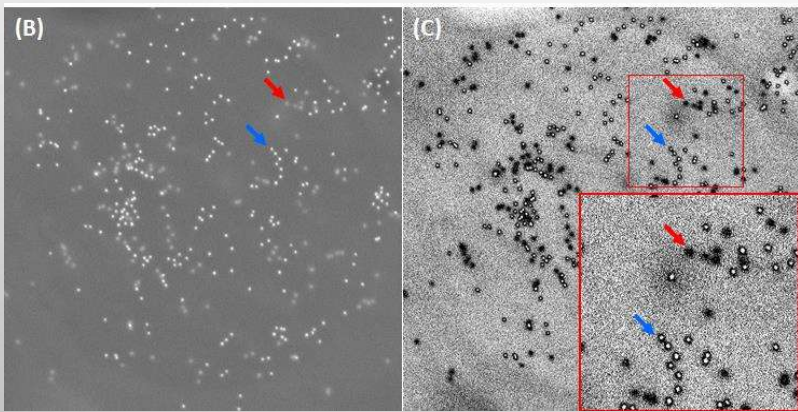
# MULTIPLE IMMUNOLABELING IN LOW-VOLTAGE STEM

THE ENHANCEMENT OF THE VISUAL DIFFERENCE BETWEEN BOTTOM AND TOP Au NPs WITH THE HELP OF IMAGE PROCESSING

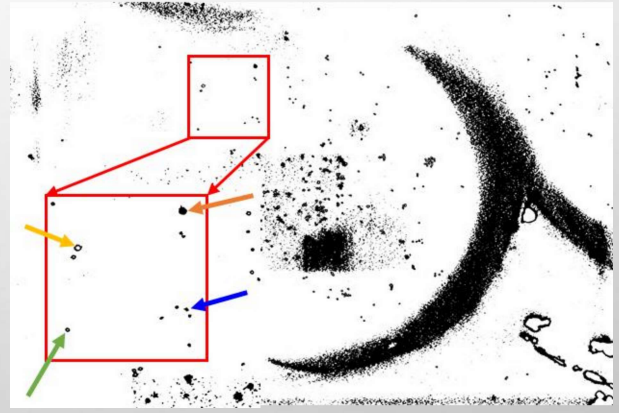
BSE image → Import to ImageJ/FIJI → Adjust the B/W threshold → Upper NPs will transform to donut shape



adjust the minima and maxima of the B/W threshold



10 nm NPs, 5kV, 15.68μs, 37 000x, 100 nm section



10 or 15 nm NPs, 5kV, 10μs, 20 000x, 100 nm section

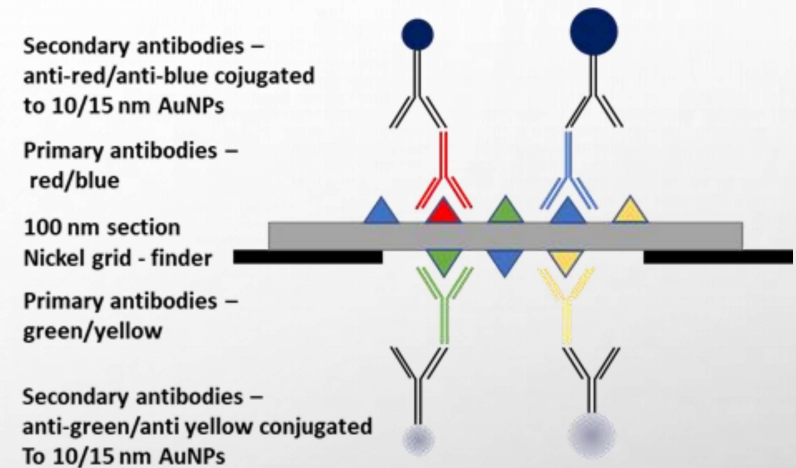
**This approach works not only for particles of the same diameter, but also for the particles of different diameters; though, each size needs a bit different B/W threshold setting**



# MULTIPLE IMMUNOLABELING IN LOW-VOLTAGE STEM

## SUMMARY

- THIS METHOD ALLOWS DOING STRIGHTFORWARD DOUBLE IMMUNO-LOCALIZATION, EVEN WHEN HAVING PRIMARY ANTIBODIES FROM THE SAME SPECIES – WITH SINGLE ACCELERATING VOLTAGE
- WITH THIS APPROACH THE NUMBER OF LABELLED BIOMOLECULES ARE EFFECTIVELY DOUBLED (2 Au MARKER SIZES VISUALIZE 4 BIOMOLECULES, 3→6, 4→8...)
- THE VISUAL DIFFERENCE CAN BE FURTHER ENHANCED BY COMMONLY AVAILABLE SOFTWARE



# MULTIPLE IMMUNOLABELING IN LOW-VOLTAGE STEM

## Acknowledgements:

### Laboratory of Electron Microscopy in České Budějovice

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Martina Tesařová

Jiří Vaněček

Jan Langhans

Zdeno Gardian

Eva Ďurinová

Jana Kopecká

### Institute of Parasitology:

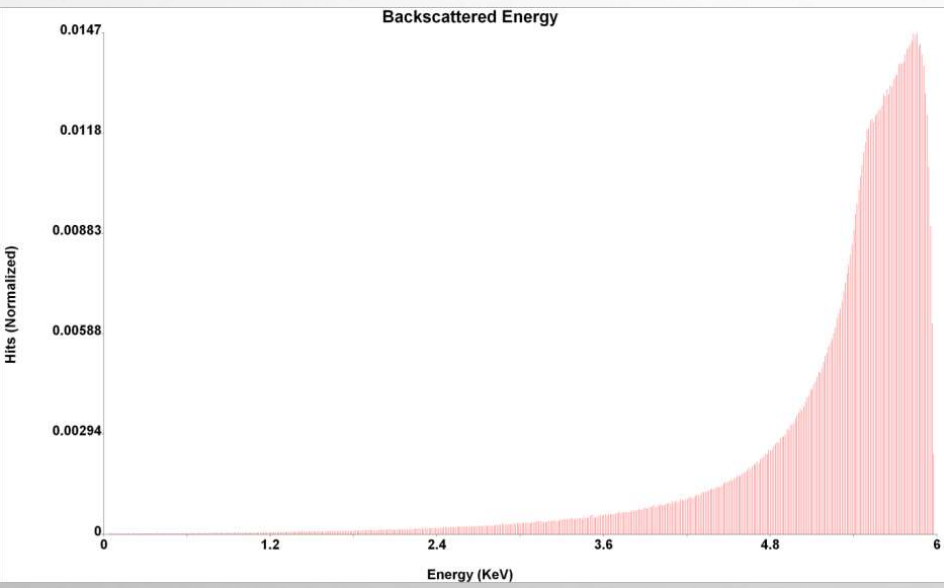
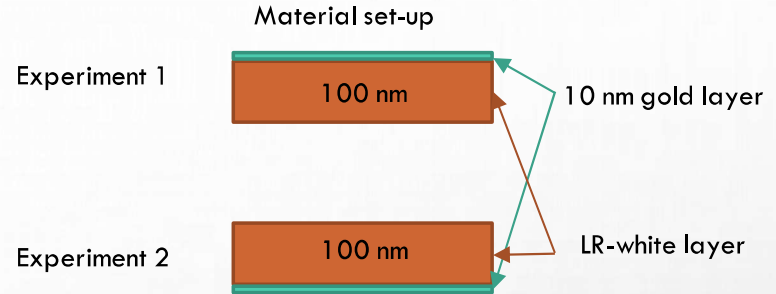
Shun-Min Yang



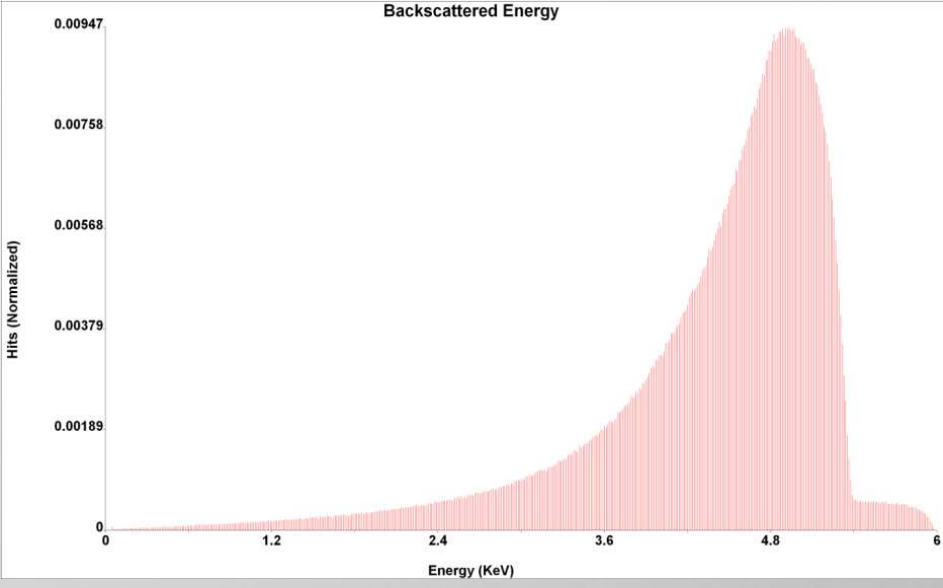
THANK YOU FOR YOUR ATTENTION

# MULTIPLE IMMUNOLABELING IN LOW-VOLTAGE STEM

## MC SIMULATION OF THE BSE SIGNAL



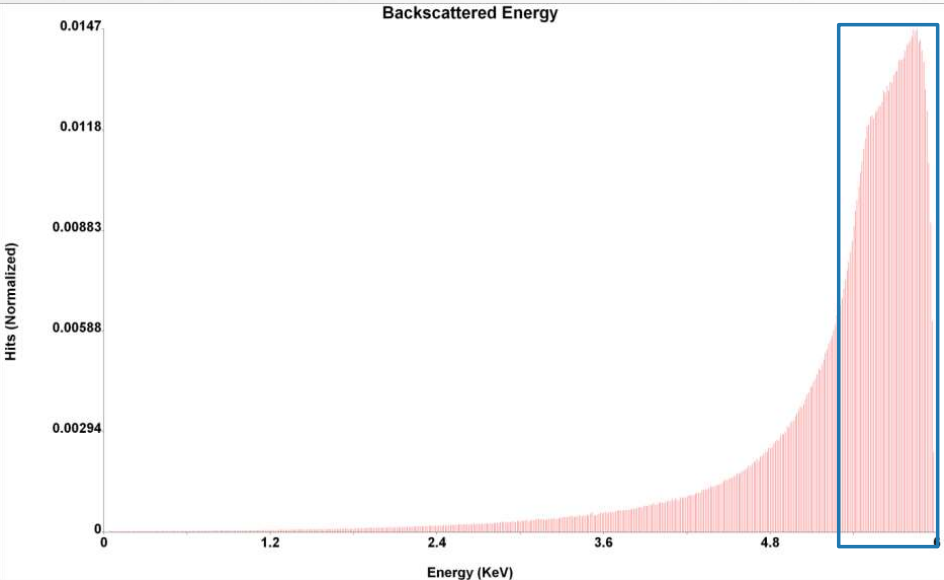
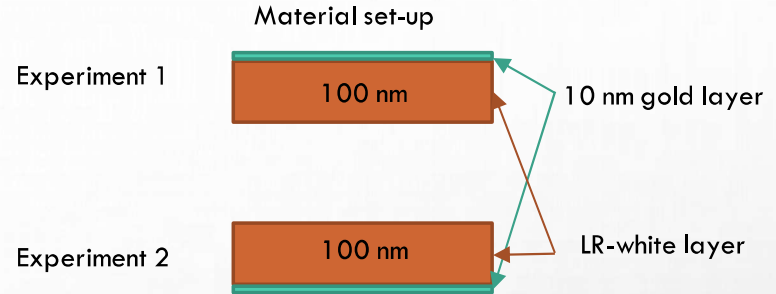
Experiment 1: BSE signal from the gold on top, 6 kV, 10 000 000 electrons



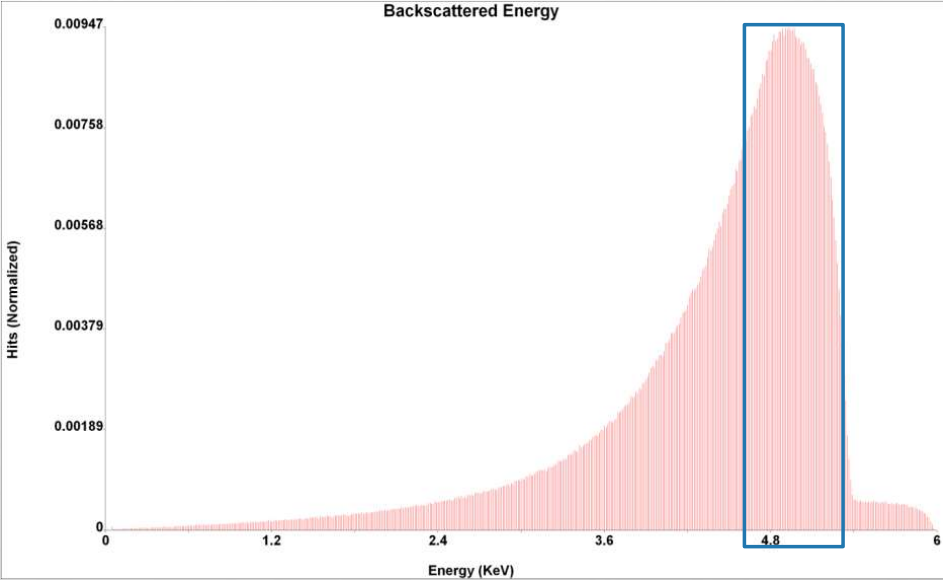
Experiment 2: BSE signal from the gold below the section, 6 kV, 10 000 000 electrons

# MULTIPLE IMMUNOLABELING IN LOW-VOLTAGE STEM

## MC SIMULATION OF THE BSE SIGNAL



Experiment 1: BSE signal from the gold on top, 6 kV, 10 000 000 electrons

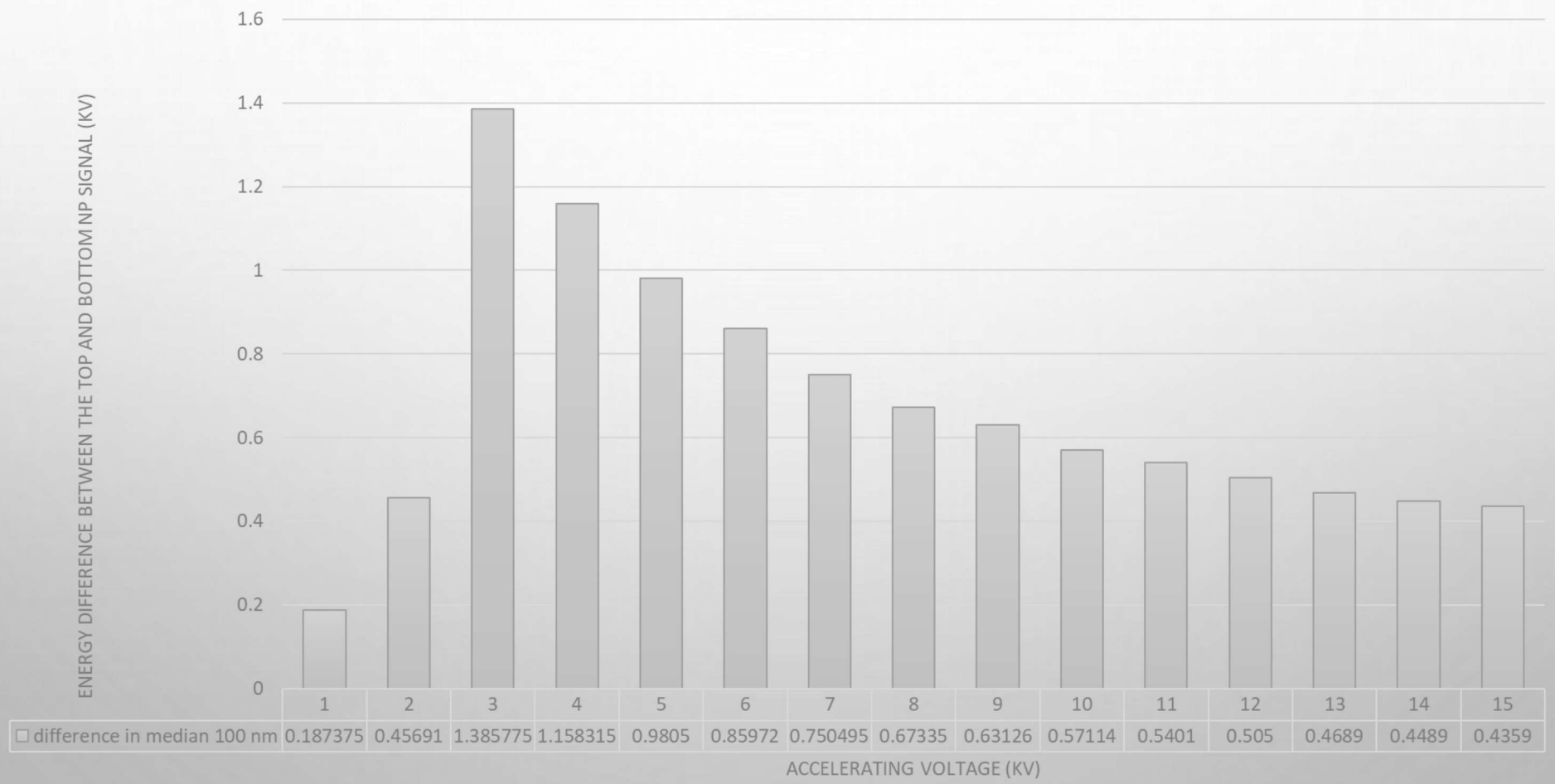


Experiment 2: BSE signal from the gold below the section, 6 kV, 10 000 000 electrons

# MULTIPLE IMMUNOLABELING IN LOW-VOLTAGE STEM

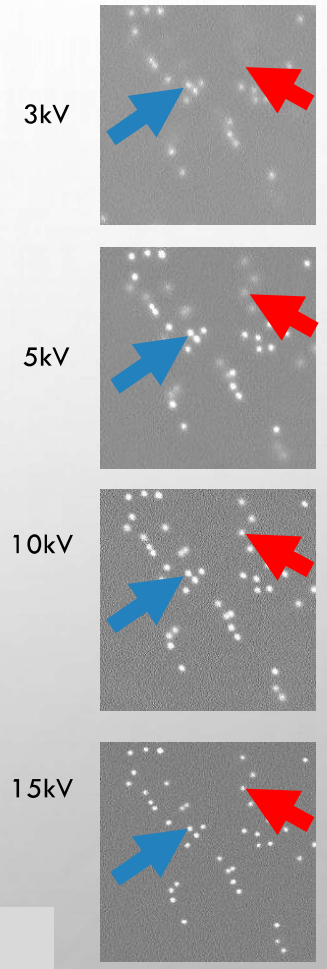
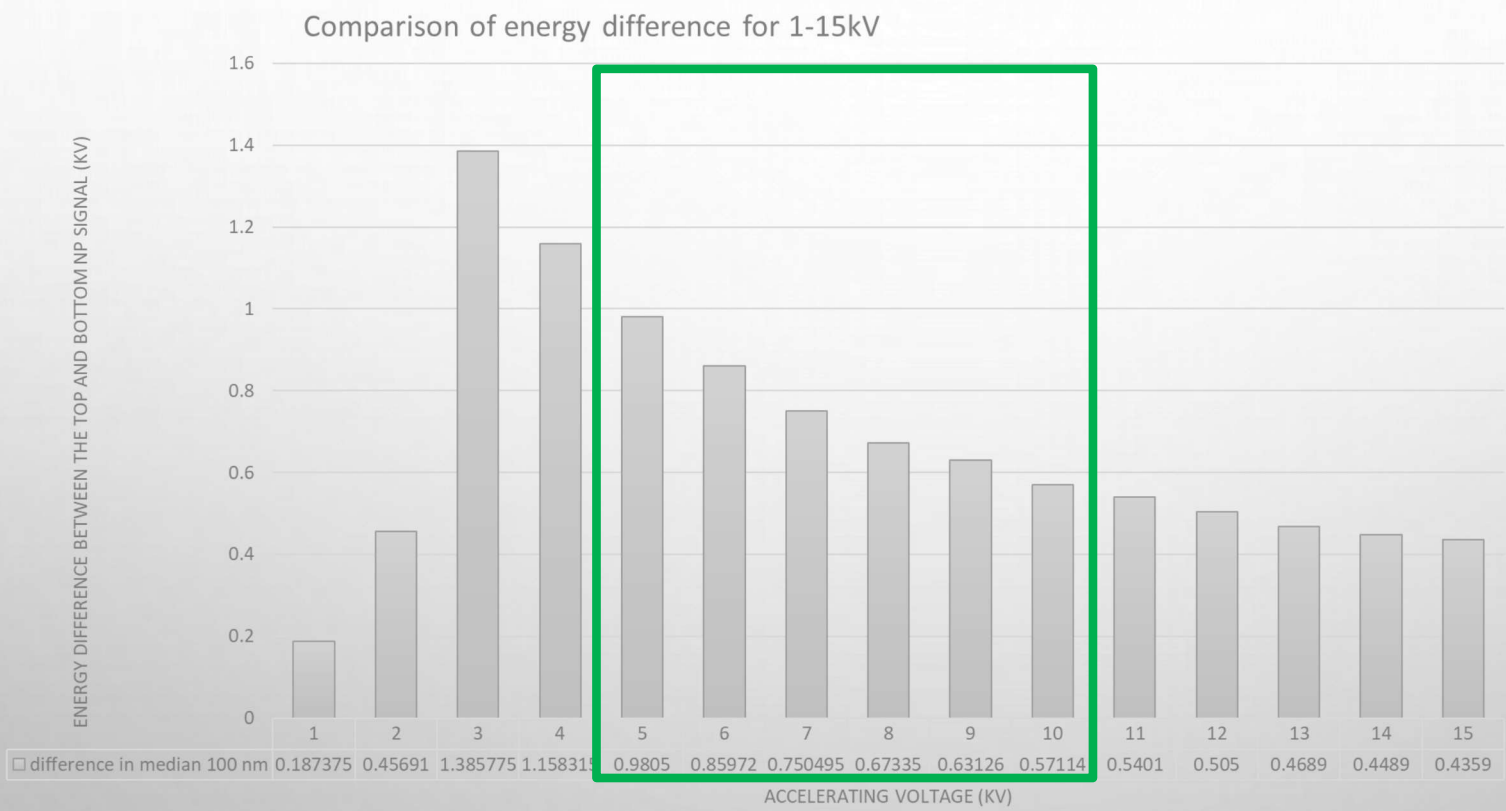
## MC SIMULATION OF THE BSE SIGNAL

Comparison of energy difference for 1-15kV



# MULTIPLE IMMUNOLABELING IN LOW-VOLTAGE STEM

## MC SIMULATION OF THE BSE SIGNAL



**There is a certain energy difference between the BSE signal from the top and bottom NP depending on the accelerating voltage.**